

Listing of Claims and Amendments thereto:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of producing an acoustic resonator device, comprising:
- depositing a first metal film on a substrate;
 - patterning said first metal film;
 - depositing piezoelectric material on said first metal film;
 - depositing a second metal film on said piezoelectric material;
 - patterning said second metal film to form a complete acoustic resonator device; and
 - ~~isolating said piezoelectric material by selectively removing some or all piezoelectric material not involved in signal transmission after said acoustic resonator device is formed by a selective etching process to limit lateral propagation losses to un-etched regions of the formed acoustic resonator device~~
~~reduce an amount of acoustic energy which propagates in a lateral direction away from the device.~~
2. (Cancel) The method of claim 1, wherein said isolation of said piezoelectric material is performed during fabrication of the device.
3. (Cancel) The method of claim 1, wherein said isolation of said piezoelectric material is performed after fabrication of the device.
4. (Cancel) The method of claim 1, wherein said step of isolating further includes removing some or all piezoelectric material not involved in signal transmission after device fabrication to limit lateral propagation losses to un-etched regions of the device.
5. (Cancel) The method of claim 4, wherein said step of removing is performed by a selective etching process.

Claims 6-9 (Withdrawn)

10. (Original) The method of claim 1, wherein said piezoelectric material is selected from the group comprising at least AlN, ZnO and CdS.
11. (Currently Amended) The method of claim 1, wherein said ~~conductive~~ first and second metal films are formed by lithographic patterning of Al metal or other conductors.
12. (Previously Amended) The method of claim 1, wherein said substrate is formed as a plurality of acoustic reflecting layers on a substrate such as a silicon, quartz, or glass wafer.
13. (Currently Amended) A method of isolating an acoustic resonator device, comprising:
depositing a first metal film on a substrate;
~~patterning said first metal film;~~
depositing piezoelectric material on said first metal film;
depositing a second metal film on said piezoelectric material to form a complete acoustic resonator device;
~~patterning said second metal film; and~~
removing some or all piezoelectric material not involved in signal transmission with a selective etching process that is performed after said acoustic resonator device is formed, to limit device fabrication to limit lateral propagation losses to un-etched regions of the device, thereby limiting propagation of energy in lateral modes.
14. (Cancel) The method of claim 13, wherein said step or removing is performed by a elective etching process.
15. (Currently Amended) The method of claim ~~14~~ 13, wherein at least some of the substrate surface is removed by selective etching.
16. (Original) The method of claim 13, wherein at least some of the removed piezoelectric material forms a void which is back filled with a different material.

Claims 17-28 (Withdrawn)

29. (New) The method of claim 1, wherein said deposited piezoelectric material is deposited as a continuous layer on said first metal film.

30. (New) The method of claim 29, wherein the continuous piezoelectric layer is not patterned.

31. (New) The method of claim 13, wherein said deposited piezoelectric material is deposited as a continuous layer on said first metal film.

32. (New) The method of claim 31, wherein the continuous piezoelectric layer is not patterned.

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